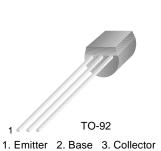


SEMICONDUCTOR®

KSP62/63/64

Darlington Transistor

- Collector-Emitter Voltage: V_{CES}=KSP62: 20V
- KSP63/64: 30V
- + Collector Power Dissipation: P_C (max)=625mW



PNP Epitaxial Silicon Darlington Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

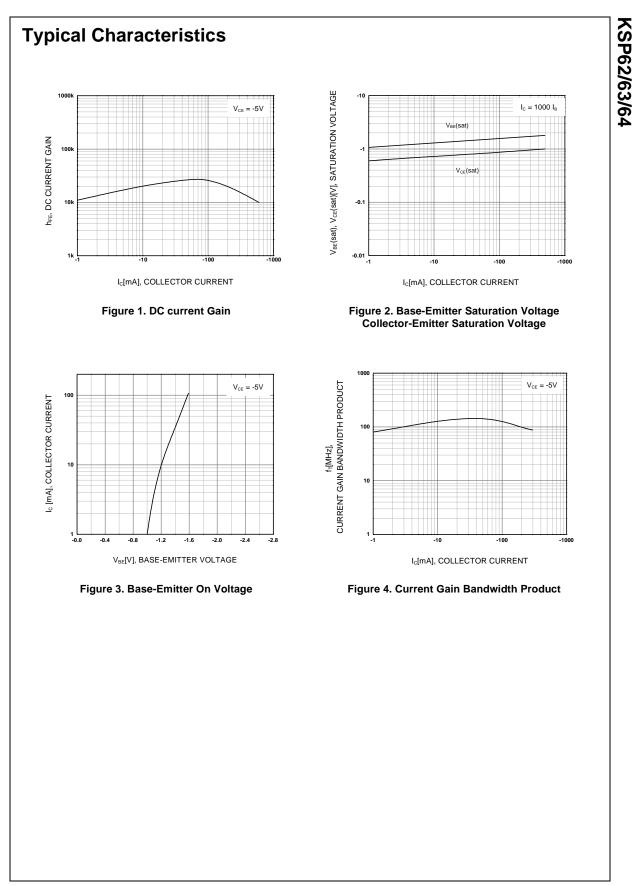
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: KSP62	-20	V
	: KSP63/64	-30	V
V _{CEO}	Collector-Emitter Voltage		
010	: KSP62	-20	V
	: KSP63/64	-30	V
V _{EBO}	Emitter-Base Voltage	-10	V
I _C	Collector Current	-500	mA
I _C P _C	Collector Power Dissipation	625	mW
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55~150	°C

Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CES}	Collector-Emitter Breakdown Voltage	I _C = -100μA, I _B =0			
	: KSP62		-20		V
	: KSP63/64		-30		V
I _{CBO}	Collector Cut-off Current				
	: KSP62	V _{CB} = -15V, I _E =0		-100	nA
	: KSP63/64	$V_{CB} = -30V, I_{E} = 0$		-100	nA
I _{EBO}	Emitter Cut-off Current	V _{BE} = -10V, I _C =0		-100	nA
h _{FE}	* DC Current Gain				
	: KSP62	V _{CE} = -5V, I _C = -10mA	20K		
	: KSP63		5K		
	: KSP64		10K		
	: KSP63	V _{CE} = -5V, I _C = -100mA	10K		
	: KSP64	02 0	20K		
V _{CE} (sat)	* Collector-Emitter Saturation Voltage				
	: KSP62	I _C = -10mA, I _B = -0.01mA		-1.0	V
	: KSP63/64	I _C = -100mA, I _B = -0.1mA		-1.5	V
V _{BE} (on)	* Base-Emitter On Voltage				
	: KSP62	V _{CE} = -5V, I _C = -10mA		-1.4	V
	: KSP63/64	V _{CE} = -5V, I _C = -100mA		-2	V
f _T	Current Gain Bandwidth Product	V _{CE} = -5V, I _C = -100mA	125		MHz
	: KSP63/64	f=100MHz			

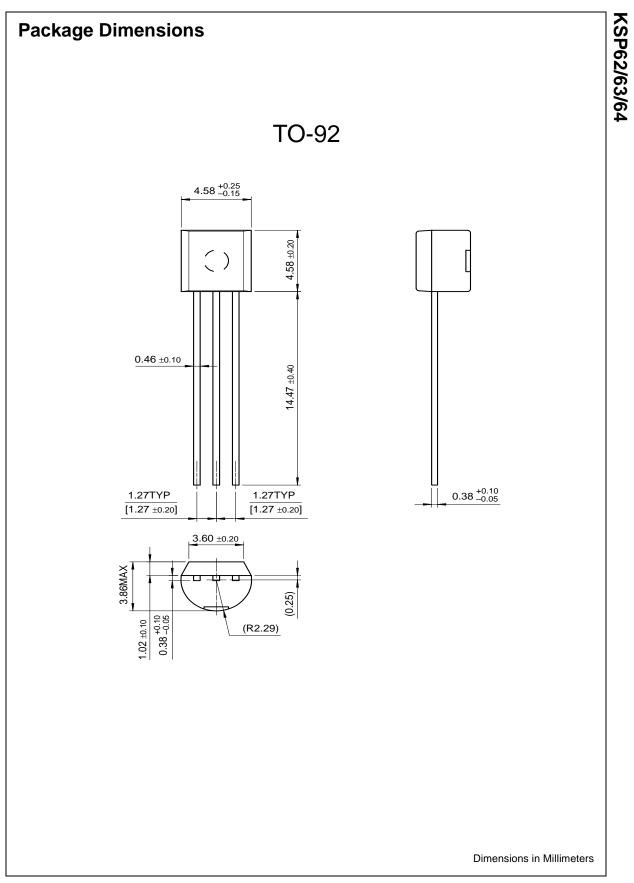
KSP62/63/64

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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